
HZM27FA

Silicon Epitaxial Planar Zener Diode for Surge Absorb

HITACHI

ADE-208-443A(Z)

Rev 1

September 1996

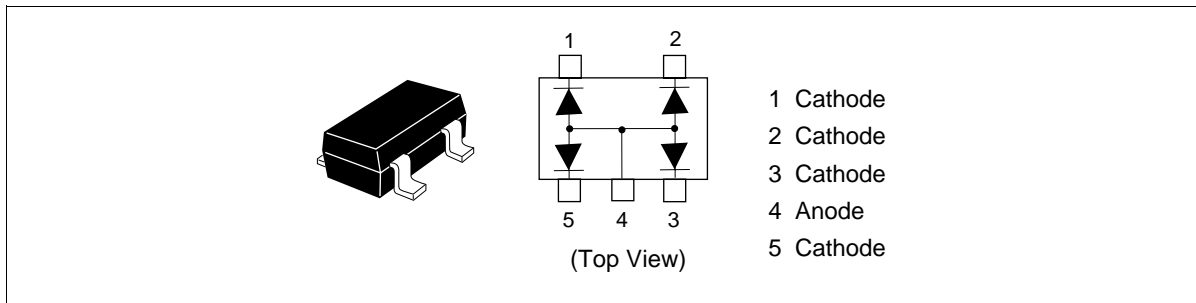
Features

- HZM27FA has four devices, and can absorb external + and -surge.
- MPAK Package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HZM27FA	27A	MPAK-5

Outline



HZM27FA

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Power dissipation	Pd *1	200	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

Note 1. Four device total, With P.C board.

Electrical Characteristics (Ta = 25°C) *1

tem	Symbol	Min	Typ	Max	Unit	Test Condition
Zener voltage	VZ	25.10	∅	28.90	V	IZ = 2 mA, 40ms pulse
Reverse current	IR	∅	∅	2	μA	VR = 21V
Capacitance	C	∅	(27) *3	∅	pF	VR = 0V, f = 1 MHz
Dynamic resistance	r d	∅	∅	70	Ω	IZ = 2 mA
ESD-Capability	∅	30	∅	∅	kV	C = 150pF, R = 330 Ω, Both forward and reverse direction 10 pulse *2

- Notes
1. Per one device.
 2. Failure criterion ; IR ∅ 2 μA at VR = 21V.
 3. Reference only.

Main Characteristic

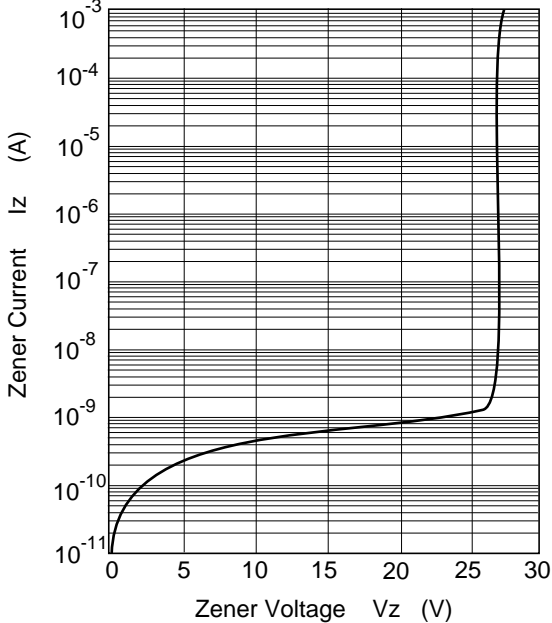


Fig.1 Zener current Vs. Zener voltage

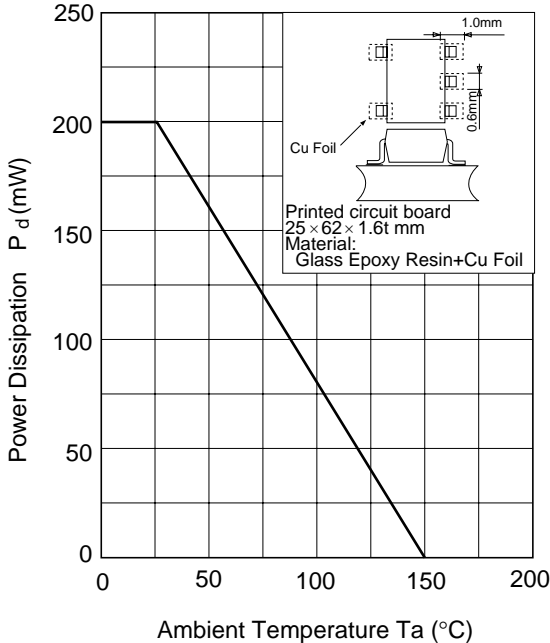


Fig.2 Power Dissipation Vs. Ambient Temperature

HZM27FA

Package Dimensions

Unit : mm

